

Amplifier Transistors NPN Silicon

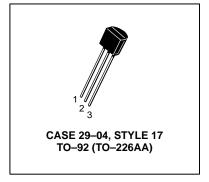
MAXIMUM RATINGS

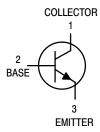
Rating	Symbol	BC546	BC547	BC548	Unit
Collector–Emitter Voltage	VCEO	65	45	30	Vdc
Collector–Base Voltage	VCBO	80	50	30	Vdc
Emitter-Base Voltage	VEBO	6.0			Vdc
Collector Current — Continuous	IC	100			mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	PD	625 5.0			mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	PD	1.5 12			Watt mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150			°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction to Case	R ₀ JC	83.3	°C/W

BC546BBC547ABC547BBC547CBC548BBC548C





ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic		Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS						
Collector–Emitter Breakdown Voltage (I _C = 1.0 mA, I _B = 0)	BC546 BC547 BC548	V(BR)CEO	65 45 30	_ _ _	_ _ _	V
Collector–Base Breakdown Voltage (I _C = 100 μAdc)	BC546 BC547 BC548	V(BR)CBO	80 50 30	_ _ _	_ _ _	V
Emitter–Base Breakdown Voltage (I _E = 10 μA, I _C = 0)	BC546 BC547 BC548	V(BR)EBO	6.0 6.0 6.0	_ _ _	_ _ _	V
Collector Cutoff Current (VCE = 70 V, VBE = 0) (VCE = 50 V, VBE = 0) (VCE = 35 V, VBE = 0) (VCE = 30 V, TA = 125°C)	BC546 BC547 BC548 BC546/547/548	ICES	_ _ _ _	0.2 0.2 0.2 —	15 15 15 4.0	nA μA

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted) (Continued)

Characteristic		Symbol	Min	Тур	Max	Unit
ON CHARACTERISTICS		•	•	•	•	
DC Current Gain (IC = 10 μ A, VCE = 5.0 V)	BC547A BC546B/547B/548B BC548C	hFE	_ _ _	90 150 270	_ _ _	_
$(I_C = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V})$	BC546 BC547 BC548 BC547A BC546B/547B/548B BC547C/BC548C		110 110 110 110 200 420		450 800 800 220 450 800	
$(I_C = 100 \text{ mA}, V_{CE} = 5.0 \text{ V})$	BC547A/548A BC546B/547B/548B BC548C		_ _ _	120 180 300	_ _ _	
Collector–Emitter Saturation Voltage (I _C = 10 mA, I _B = 0.5 mA) (I _C = 100 mA, I _B = 5.0 mA) (I _C = 10 mA, I _B = See Note 1)		VCE(sat)	_ _ _	0.09 0.2 0.3	0.25 0.6 0.6	V
Base–Emitter Saturation Voltage (I _C = 10 mA, I _B = 0.5 mA)		VBE(sat)	_	0.7	_	V
Base–Emitter On Voltage (I _C = 2.0 mA, V _{CE} = 5.0 V) (I _C = 10 mA, V _{CE} = 5.0 V)		VBE(on)	0.55 —		0.7 0.77	V
SMALL-SIGNAL CHARACTERISTICS						
Current–Gain — Bandwidth Product (I _C = 10 mA, V _{CE} = 5.0 V, f = 100 MHz)	BC546 BC547 BC548	fΤ	150 150 150	300 300 300	_ _ _	MHz
Output Capacitance (V _{CB} = 10 V, I _C = 0, f = 1.0 MHz)		C _{obo}	_	1.7	4.5	pF
Input Capacitance (V _{EB} = 0.5 V, I _C = 0, f = 1.0 MHz)		C _{ibo}	_	10	_	pF
Small–Signal Current Gain ($I_C = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V}, f = 1.0 \text{ kHz}$)	BC546 BC547/548 BC547A BC546B/547B/548B BC547C/548C	h _{fe}	125 125 125 240 450		500 900 260 500 900	_
Noise Figure (I _C = 0.2 mA, V_{CE} = 5.0 V, R _S = 2 k Ω , f = 1.0 kHz, Δ f = 200 Hz)	BC546 BC547 BC548	NF	_ _ _	2.0 2.0 2.0	10 10 10	dB

Note 1: I_B is value for which I_C = 11 mA at V_{CE} = 1.0 V.

BC547/BC548

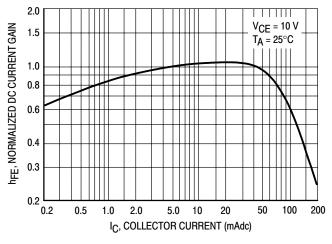


Figure 1. Normalized DC Current Gain

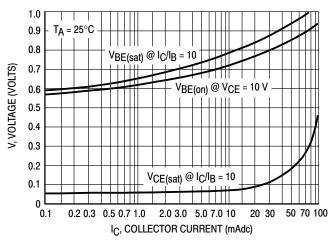


Figure 2. "Saturation" and "On" Voltages

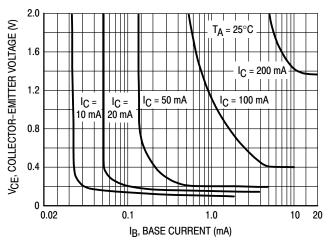


Figure 3. Collector Saturation Region

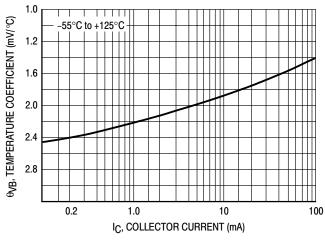


Figure 4. Base-Emitter Temperature Coefficient

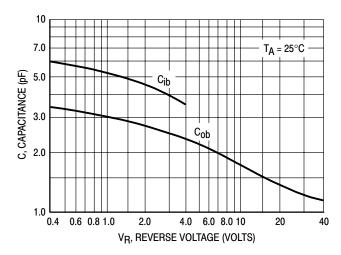


Figure 5. Capacitances

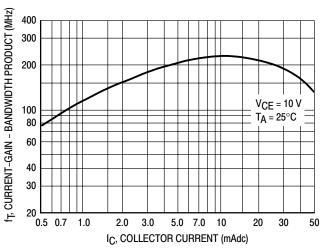


Figure 6. Current-Gain - Bandwidth Product

BC546

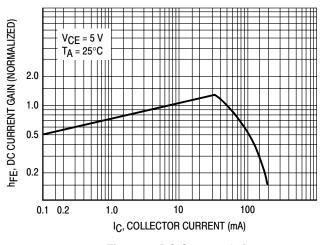


Figure 7. DC Current Gain

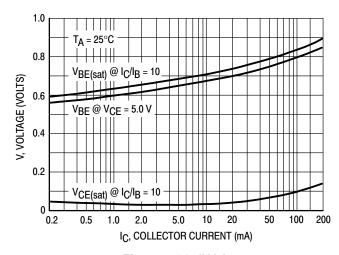


Figure 8. "On" Voltage

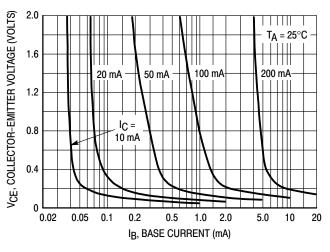


Figure 9. Collector Saturation Region

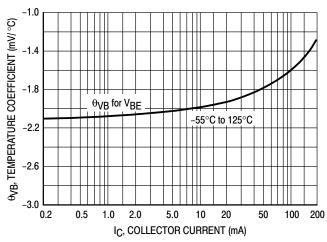


Figure 10. Base-Emitter Temperature Coefficient

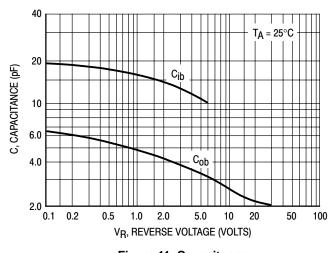


Figure 11. Capacitance

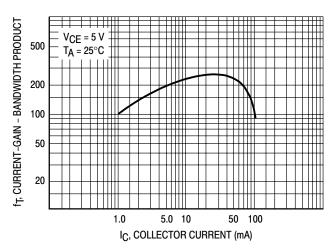
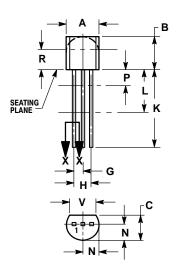


Figure 12. Current-Gain - Bandwidth Product

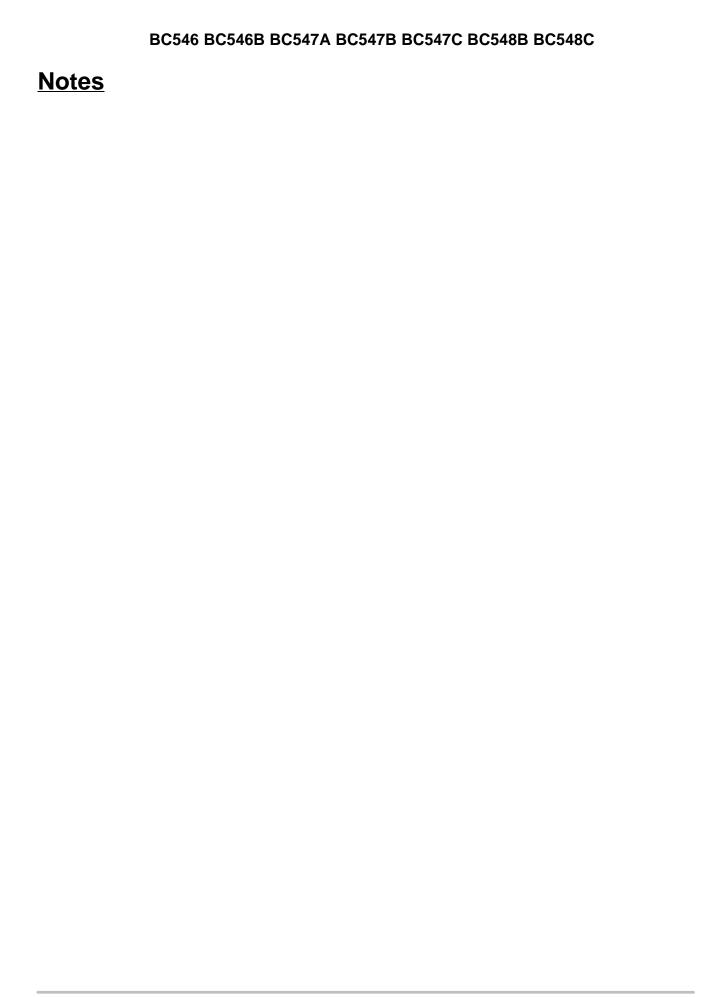
PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 ISSUE AL



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
 4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INC	HES	MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.175	0.205	4.45	5.20	
В	0.170	0.210	4.32	5.33	
С	0.125	0.165	3.18	4.19	
D	0.016	0.021	0.407	0.533	
G	0.045	0.055	1.15	1.39	
Н	0.095	0.105	2.42	2.66	
7	0.015	0.020	0.39	0.50	
K	0.500		12.70		
L	0.250		6.35		
N	0.080	0.105	2.04	2.66	
P		0.100		2.54	
R	0.115		2.93		
٧	0.135		3.43		





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